Figure 6: Temperature dependences of current for fixed voltages on a Ni-silicide/poly-Si Schottky diode and temperature coefficient of signal (current) for each branch of the $I$–$V$ characteristics: (a) forward and (b) reverse currents (the legend represents the applied bias in volts for each line); (c) temperature coefficient of current vs fixed voltage on the structure; negative and positive values of $U$ in panel (c) correspond to forward and reverse biasing, respectively.